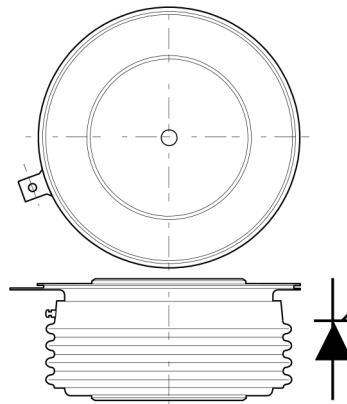


Phase Control Thyristor

multicomp PRO

**RoHS
Compliant**



Outline type code: G

Features

- Double Side Cooling
- High Surge Capability

Applications

- High Power Drives
- High Voltage Power Supplies
- Static Switches

Key Parameters						
Part Number	Repetitive Peak Voltages V_{DRM} and V_{RRM} V	$I_{T(AV)}$	I_{TSM}	dV/dt^*	dI/dt	Conditions
MPPCT1010G140	1400	1010 A	15000 A	1000 V/ μ s	200 A/ μ s	$T_{vj} = -40^{\circ}\text{C}$ to 125°C , $I_{DRM} = I_{RRM} = 60\text{mA}$, $V_{DRM}, V_{RRM} t_p = 10\text{ms}$, $V_{DSM} \& V_{RSM} =$ $V_{DRM} \& V_{RRM} + 100\text{V}$ respectively

Current Ratings

$T_{case} = 60^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
$I_{T(AV)}$	Surge (non-repetitive) on-state current	Half wave resistive load	1010	A
$I_{T(RMS)}$	RMS value	-	1590	
I_T	Continuous (direct) on-state current	-	1430	

Surge Ratings

Symbol	Parameter	Test Conditions	Max.	Units
I_{TSM}	Mean on-state current	10ms half sine, $T_{case} = 125^{\circ}\text{C}$ $V_R = 0$	15	kA
I^2t	I^2t for fusing		1.13	MA^2s

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Thermal and Mechanical Ratings

Symbol	Parameter	Test Conditions	Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance – junction to case	Double side cooled DC	-	0.035	°C/W
$R_{th(c-h)}$	Thermal resistance – case to heatsink		-	0.008	
T_{vj}	Virtual junction temperature	Blocking V_{DRM} / V_{RRM}	-	125	°C
T_{stg}	Storage temperature range		-40	140	
F_m	Clamping force		12	18	kN

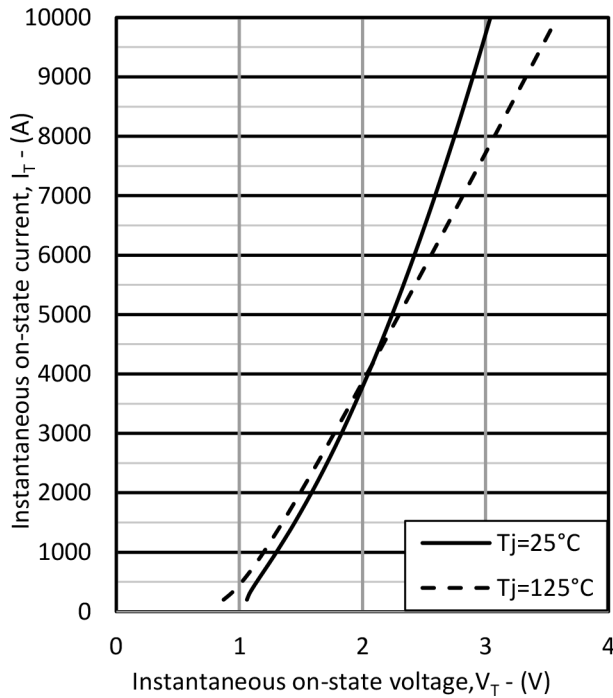
Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min.	Max.	Units
I_{RRM}/I_{DRM}	Peak reverse and off-state current	At V_{RRM}/V_{DRM} , $T_{case} = 125^{\circ}C$	-	60	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125^{\circ}C$, gate open	1000	-	V/ μ s
di/dt	Rate of rise of on-state current	From 67% V_{DRM} to 1000A Gate source 30V, 10 Ω , $t_r < 0.5\mu$ s, $T_j = 125^{\circ}C$	Repetitive 50Hz	200	A/ μ s
			Non-repetitive	1000	
V_T	On-state voltage	$I_T = 1500A$, $T_{case} = 125^{\circ}C$	-	1.35	V
$V_{T(TO)}$	Threshold voltage – Low level	$T_{case} = 125^{\circ}C$	-	0.85	
r_T	On-state slope resistance – Low level	$T_{case} = 125^{\circ}C$	-	0.33	m Ω
t_{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10 Ω $t_r = 0.5\mu$ s, $T_j = 25^{\circ}C$	-	3	μ s
t_q	Turn-off time	$T_j = 125^{\circ}C$, $V_R = 100V$, $di/dt = 10A/\mu$ s, $dV_{DR}/dt = 20V/\mu$ s linear to 67% V_{DRM}	-	200	
Q_s	Stored charge	$I_T = 1000A$, $t_p = 1000\mu$ s, $T_j = 125^{\circ}C$, $di/dt = 10A/\mu$ s,	-	1500	μ C
I_{RR}	Reverse recovery current		-	120	A
I_L	Latching current	$T_j = 25^{\circ}C$,	-	1	
I_H	Holding current	$T_j = 25^{\circ}C$,	-	200	mA

Gate Trigger Characteristics and Ratings

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	3	V
V_{GD}	Gate non-trigger voltage	At 40% V_{DRM} , $T_{case} = 125^{\circ}C$	0.3	
I_{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	300	mA
I_{GD}	Gate non-trigger current	At 40% V_{DRM} , $T_{case} = 125^{\circ}C$	20	

Performance Curves



V_{TM} EQUATION

$$V_{TM} = A + B \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

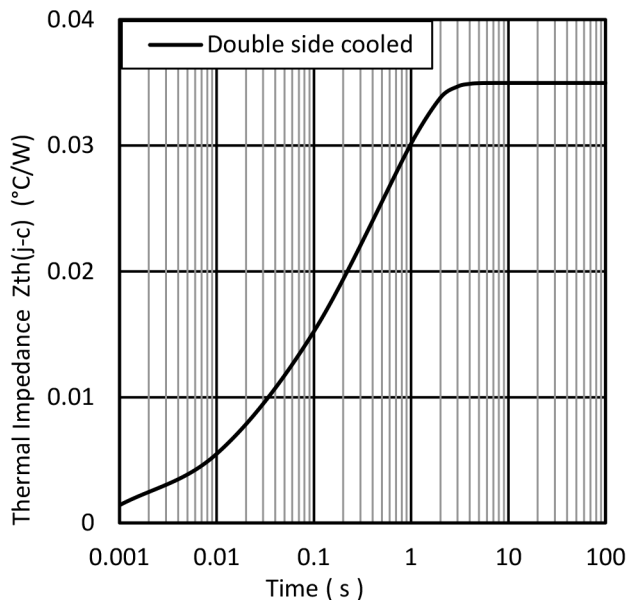
Where $A = 0.347941$

$B = 0.0934097$

$C = 0.000252939$

$D = -0.00154403$

These values are valid for $T_j = 125^\circ\text{C}$



$$R_{thjc}(t) = \sum_{i=1}^n R_{thi} \cdot \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

i	τ_i (s)	R_{thi} ($^\circ\text{C/kW}$)
1	0.7085781	19.71901
2	0.1435833	4.240625
3	0.0361520	7.963806
4	0.0021308	3.043661

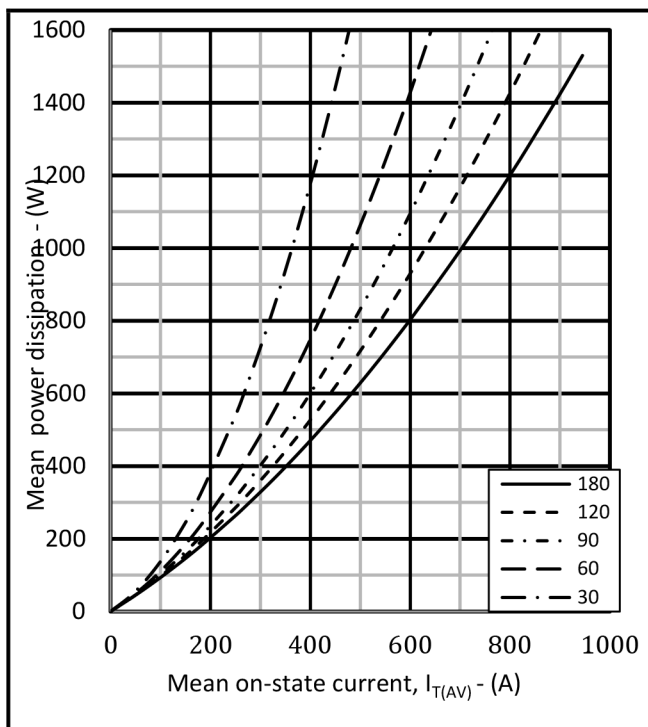


Fig.4 On-state power dissipation – sine wave

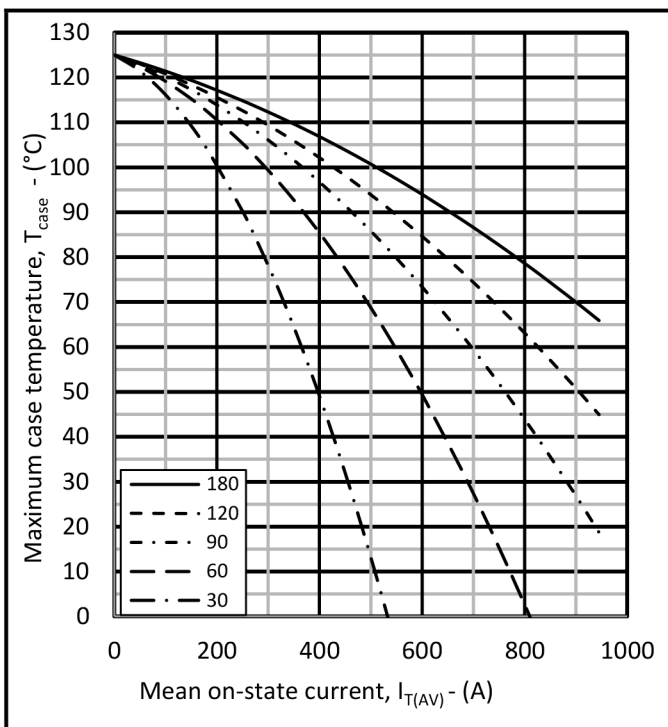


Fig.5 Maximum permissible case temperature, double side cooled – sine wave

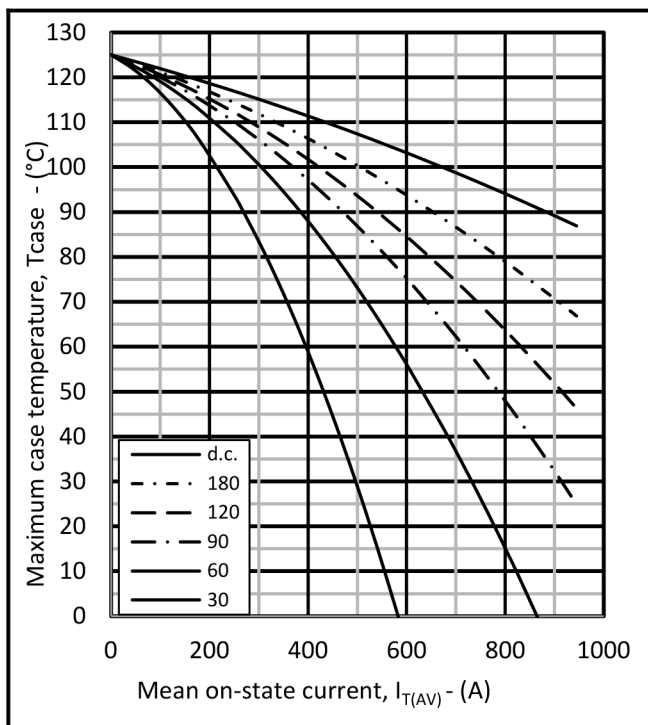


Fig.6 Maximum permissible case temperature, double side cooled – rectangular wave

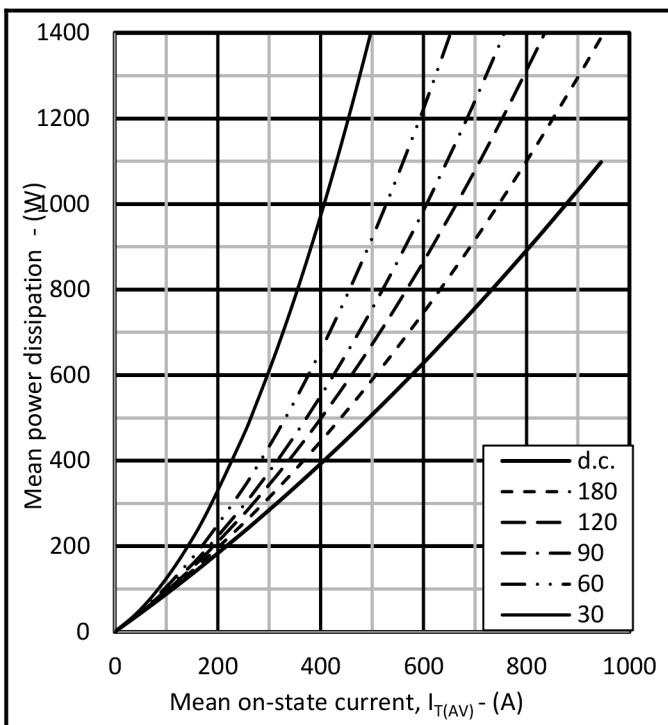


Fig.7 On-state power dissipation – rectangular wave

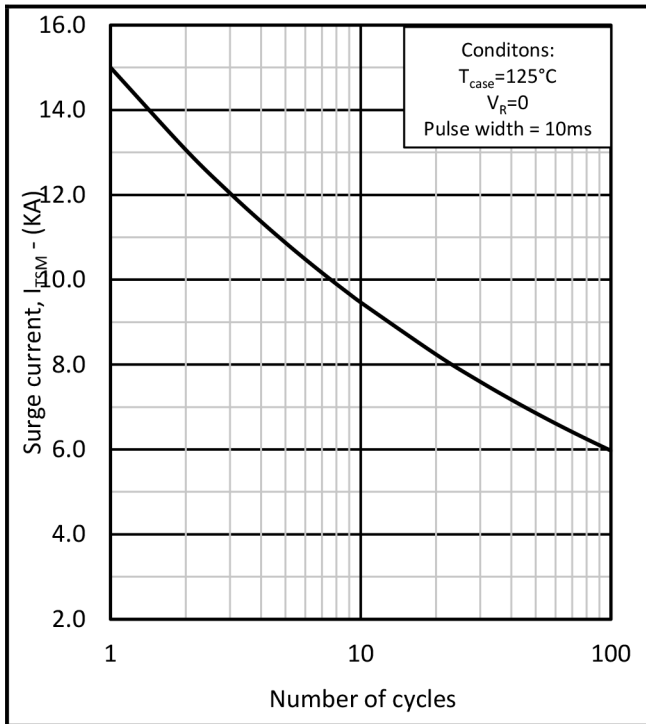


Fig.8 Multi-cycle surge current

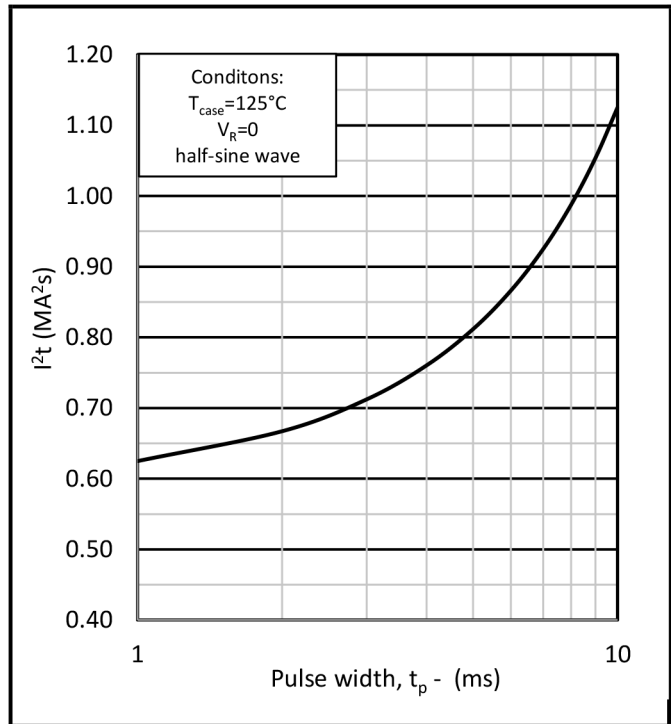


Fig.9 Single-cycle I^2t

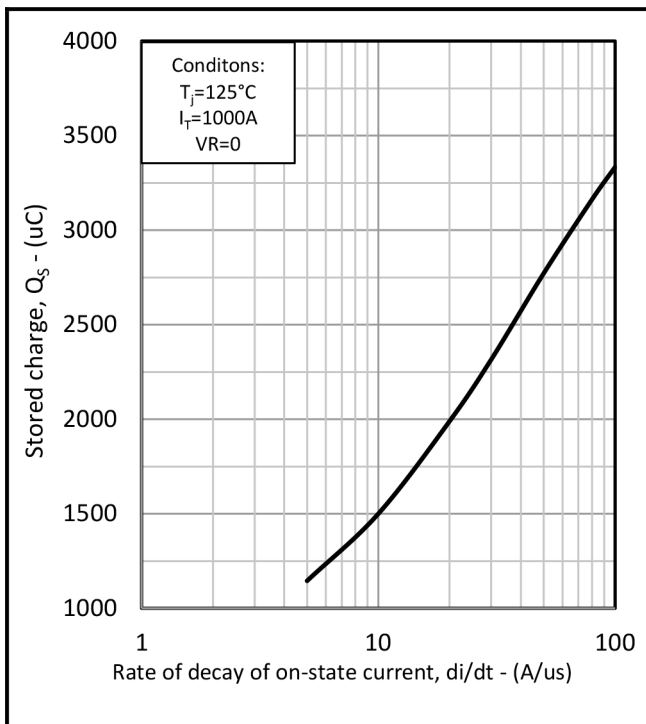


Fig.10 Stored charge vs di/dt

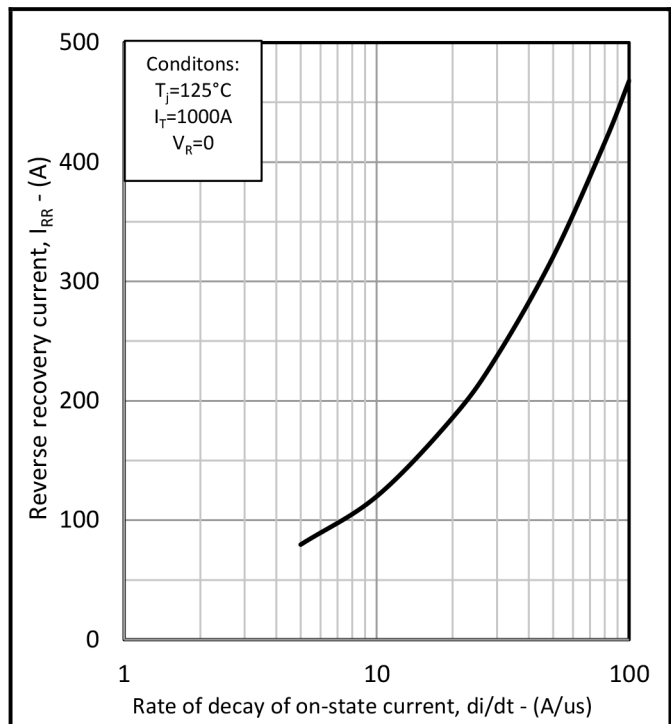


Fig.11 Reverse recovery current vs di/dt

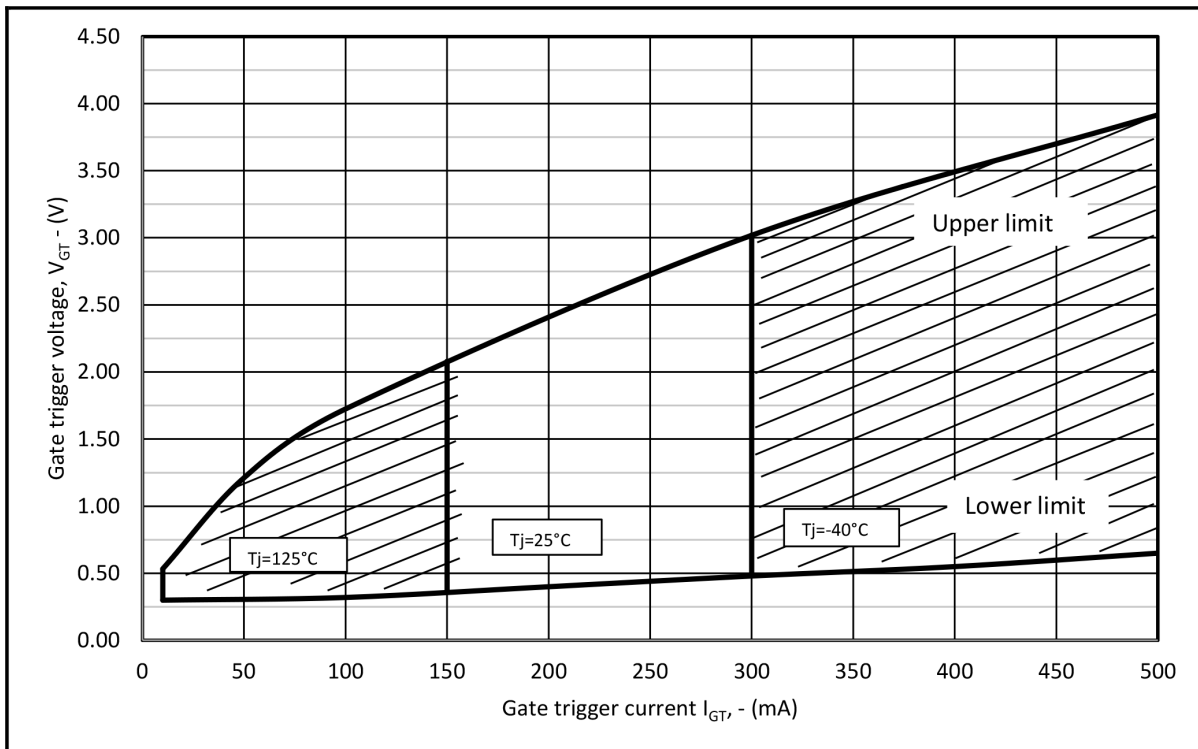
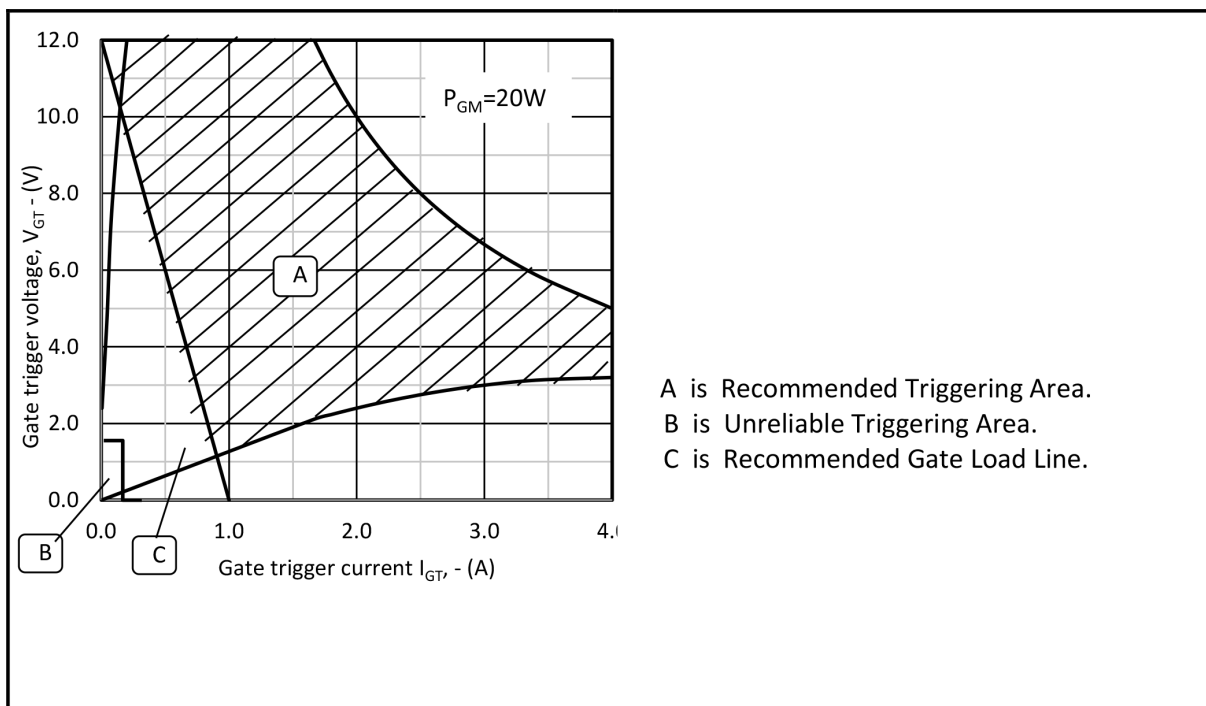


Fig.12 Gate characteristics

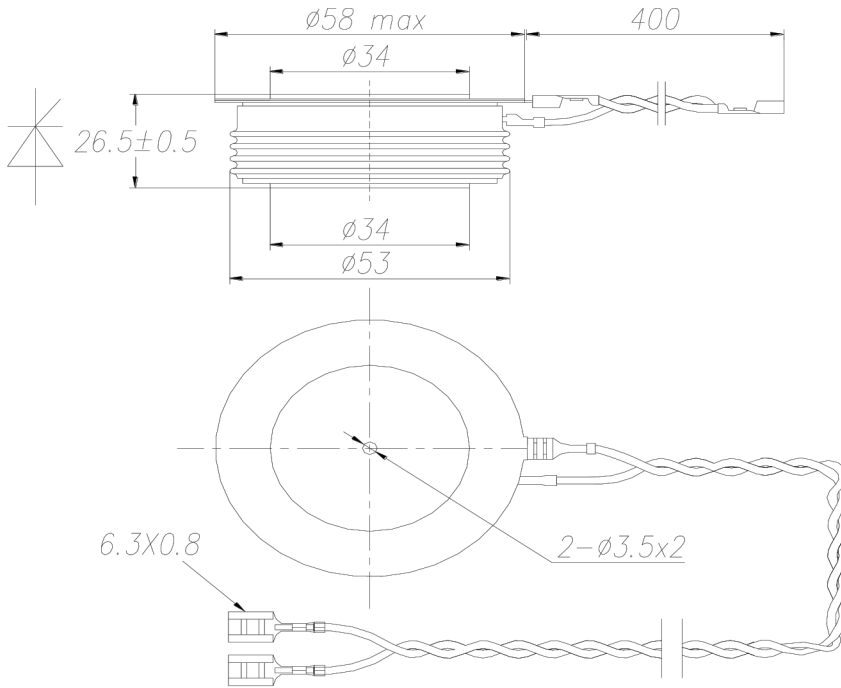


A is Recommended Triggering Area.
 B is Unreliable Triggering Area.
 C is Recommended Gate Load Line.

Fig.13 Gate characteristics

Phase Control Thyristor

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Package outline type code: G

Part Number Table

Description	Part Number
Phase Control Thyristor Module, 1400V, 1010A, G Case Code	MPPCT1010G140

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